NPN SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

ZTX658

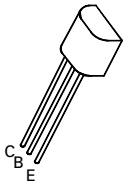
ISSUE 2 – APRIL 2002

FEATURES

* 400 Volt V_{CEO}
* 0.5 Amp continuous current
* P_{tot}=1 Watt

APPLICATIONS

* Telephone dialler circuits



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	1	A
Continuous Collector Current	I_C	500	mA
Power Dissipation at T_{amb}=25°C derate above 25°C	P_{tot}	1 5.7	W mW/ °C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	400			V	I_C=100μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO)}$	400			V	I_C=10mA*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	I_E=100μA
Collector Cut-Off Current	I_{CBO}			100	nA	V_{CB}=320V
Collector Cut-Off Current	I_{CBO}			100	nA	V_{CE}=320V
Emitter Cut-Off Current	I_{EBO}			100	nA	V_{EB}=4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3 0.25 0.5	V V V	I_C=20mA, I_B=1mA I_C=50mA, I_B=5mA* I_C=100mA, I_B=10mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	I_C=100mA, I_B=10mA*
Base-Emitter Turn On Voltage	$V_{BE(on)}$			0.9	V	IC=100mA, V_{CE}=5V*
Static Forward Current Transfer Ratio	h_{FE}	50 50 40				I_C=1mA, V_{CE}=5V* I_C=100mA, V_{CE}=5V* I_C=200mA, V_{CE}=10V*

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ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

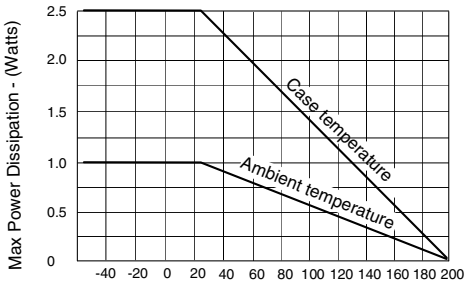
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	50			MHz	I_C=20mA, V_{CE}=20V f=20MHz
Output capcitance	C_{obo}			10	pF	V_{CB}=20V, f=1MHz
Switching times	t_{on} t_{off}		130 3300		ns ns	I_C=100mA, V_C=100V I_{B1}=10mA, I_{B2}=-20mA

* Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%

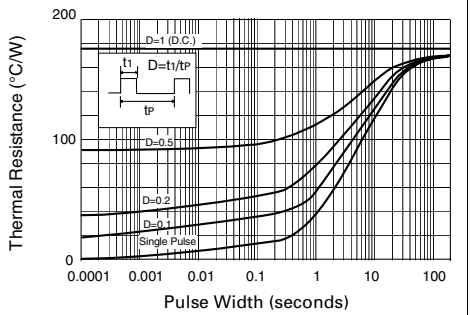
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance:Junction to Ambient$_1$	$R_{th(j\text{-}amb)1}$	175	°C/W
Junction to Ambient$_2$	$R_{th(j\text{-}amb)2}$ †	116	°C/W
Junction to Case	$R_{th(j\text{-}case)}$	70	°C/W

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

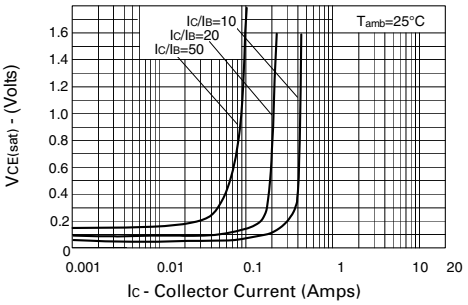


Derating curve

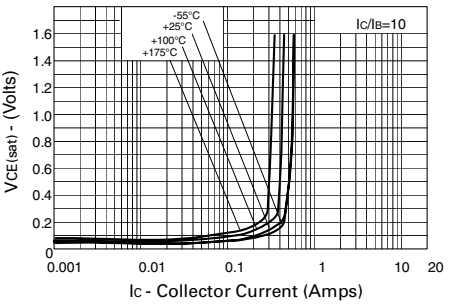


Maximum transient thermal impedance

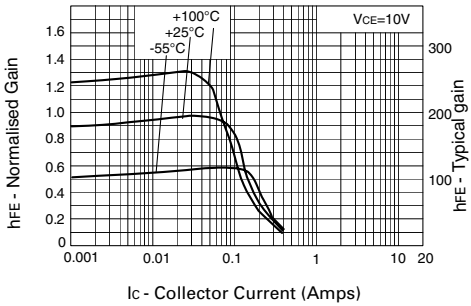
TYPICAL CHARACTERISTICS



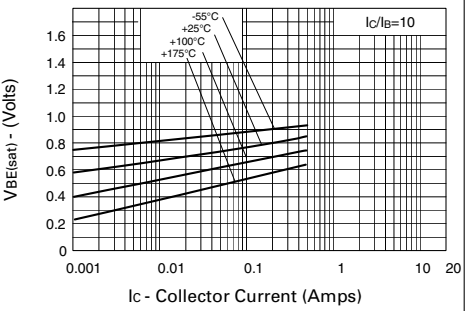
VCE(sat) v IC



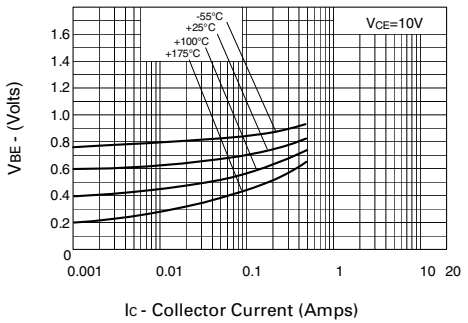
VCE(sat) v IC



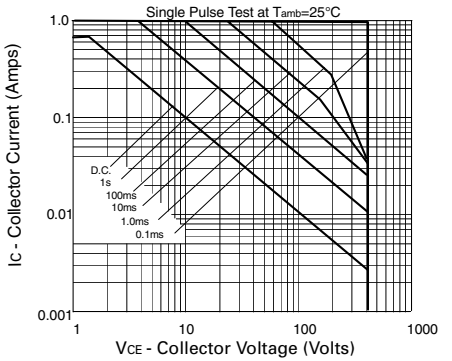
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area

单击下面可查看定价，库存，交付和生命周期等信息

>>Diodes Incorporated(达迩科技（美台）)